

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A semiconductor device comprising a connection plug ~~wherein~~ defined by a via hole filled with a metal and comprising a nanomaterial surrounded by the metal, wherein the nanomaterial is substantially uniformly disposed in a section of the ~~connection plug formed from a via hole, and the~~ metal both surrounds the nanomaterial and filled the via hole.

2. (currently amended) A semiconductor device comprising:

an insulating film (10);

an interlayer dielectric film (12) on the insulating film;

a trench within (11) the dielectric film;

an interconnection comprising

a metal layer (39) filling on the trench;

particles of metal (15) on a lower horizontal surface of the barrier metal layer;

nanotubes (14) formed on the metal particles and mixed in the metal layer,

wherein the nanotubes are of a nanomaterial ~~[[is]]~~
substantially uniformly formed on a bottom surface of the
interconnection ~~formed from a metal~~.

3. (original) The semiconductor device according to
claim 1, wherein the nanomaterial is a fibrous carbon
nanomaterial, a particle-like carbon nanomaterial or a thin
silicon wire.

4. (original) The semiconductor device according to
claim 2, wherein the nanomaterial is a fibrous carbon
nanomaterial, a granular particle-like carbon nanomaterial or a
thin silicon wire.

5. (original) The semiconductor device according to
claim 1, wherein the nanomaterial is oriented substantially
perpendicularly to a substrate.

6. (original) The semiconductor device according to
claim 2, wherein the nanomaterial is oriented substantially
perpendicularly to a substrate.

7. (original) The semiconductor device according to
claim 1, wherein the nanomaterial is provided in the whole
connection plug.

8. (original) The semiconductor device according to claim 2, wherein the nanomaterial is provided up to the vicinity of a top surface of the interconnection.

9. (original) The semiconductor device according to claim 1, wherein the metal is formed by an MOCVD method or a plating method.

10. (original) The semiconductor device according to claim 2, wherein the metal is formed by an MOCVD method or a plating method.

11-19. (canceled)

20. (original) The semiconductor device according to claim 1, wherein the connection plug formed from a metal is formed by a plating method which involves using a plating liquid containing a nanomaterial.

21. (original) The semiconductor device according to claim 2, wherein the interconnection formed from a metal is formed by a plating method which involves using a plating liquid containing a nanomaterial.

22-26. (canceled)

27. (new) A semiconductor device comprising:
an insulating film (10);
an interlayer dielectric film (12) on the insulating film;
a trench within (11) the dielectric film;
an interconnection comprising
a metal layer (39) filling the trench;
a barrier metal layer (13) coating a bottom and sides of the trench, the barrier metal layer located intermediate the metal layer and the dielectric film with the barrier metal layer separating the metal layer from the dielectric film;
particles of metal (15) on a lower horizontal surface of the barrier metal layer;
carbon nanotubes (14) formed on the metal particles and mixed in the metal layer.

28. (new) The semiconductor device according to claim 27, further comprising:
a first etching stopper layer (16) covering the dielectric film,
wherein, each of i) the trench (11), ii) the interconnection, iii) the metal layer (39), iv) the barrier metal layer (13), and the carbon nanotubes (14) extend through the first etching stopper layer.

29. (new) The semiconductor device according to claim 28, further comprising:

a second etching stopper layer (27) formed on the etching stopper layer (16), on the barrier metal layer (13), and on part of the metal layer (39);

another interlayer dielectric film (29) formed on the second etching stopper layer;

a third etching stopper layer (30) formed on the another dielectric film;

a via hole formed in the second etching stopper layer, the another dielectric film, and the third etching stopper layer;

metal (26) filling the via hole;

another barrier metal layer (28) covering a bottom and sides of the via hole and extending up to a top of the another dielectric film, the another barrier metal layer separating the metal filling the via hole from the bottom and sides of the via hole;

further metal particles on the another barrier metal layer covering the bottom of the via hole;

further carbon nanotubes (24) formed on further the metal particles and mixed in the metal filling the via hole,

wherein, said metal filling the via hole, said further carbon nanotubes, and said another barrier metal layer define a connection plug contacting said interconnection.